


Lateral power MOSFET having metal strap layer to reduce distributed resistance and method of fabricating the same

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Inventor(s): WILLIAMS RICHARD K (US)
Applicant(s): SILICONIX INC (US)
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Equivalents: ☐ [JP8264785](#), ☐ [US5767546](#)
Cited Documents: DE4037876; US5355008; US3667008; EP0624909

Abstract

To reduce the distributed resistance in an integrated circuit die, a relatively thick metal strap layer is deposited on a bus or other conductive path in the top metal layer. The metal strap layer is formed by etching a longitudinal channel in the passivation layer over the bus and plating a thick metal layer, preferably nickel, in the channel. The metal strap layer dramatically reduces the resistance of the bus. 

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